

ENSC Batch No. _____ Wafers Started _____ Date _____
 Material _____ Orientation _____ Size _____ Thickness _____
 Resistivity _____ Type _____
 Wafer Vendor _____ Vendor Batch # _____ SFU P.O. _____

Process Step #	Process Conditions	Oper & Wafer #	Comments
			Wafers must be put through a full RCA clean, per specs, immediately before this process. If necessary, use modified process to protect oxide.
___ A	Prepare Furnace Dry N2 @ 4 scfh. Ramp temp to 750/800C. Start bubbler.		
___ B	Load Wafers into Boat Use correct forceps, boat and white elephant		
___ C	Push Boat into Furnace Dry N2 @ 4 scfh. Temp = 800C. Push @ < 4"/min		
___ D	Ramp Furnace Up Dry N2 @ 4 scfh. Set operating temp		
___ E	Oxidation/Drive-in Wet N2 @ about 4 scfh, sufficient for good bubbler action. Open valve and start timing. Close valve at full time.		Desired oxide thickness = _____ microns Time = _____ min Temp = _____ C
___ F	Ramp Furnace Down Dry N2 @ 4 scfh. Temp = 400C. Bubbler off.		
___ G	Pull Boat and Unload Pull when all zones < 800C. Max pull < 4"/min		
___ H	Return Furnace to Idle Dry N2 @ 0.5-1.0 scfh		
___ I	Inspect Visual, etc.		